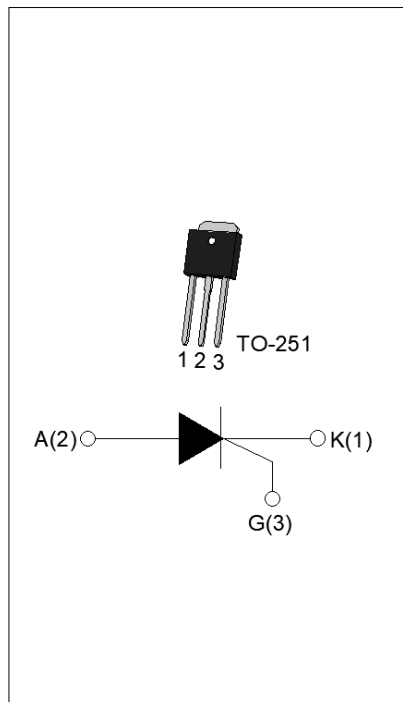




**DESCRIPTION:**

With high ability to withstand the shock loading of large current, JCT151H-800R of silicon controlled rectifiers provides high dV/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. Package TO-251 is RoHS compliant.



**MAIN FEATURES**

Symbol	Value	Unit
$I_{T(RMS)}$	12	A
$V_{DRM}/V_{RRM}$	800	V
$I_{GT}$	"15	mA

**ABSOLUTE MAXIMUM RATINGS**

Parameter	Symbol	Value	Unit
Storage junction temperature range	$T_{stg}$	-40-150	
Operating junction temperature range	$T_j$	-40-125	
Repetitive peak off-state voltage ( $T_j=25^\circ\text{C}$ )	$V_{DRM}$	800	V
Repetitive peak reverse voltage ( $T_j=25^\circ\text{C}$ )	$V_{RRM}$	800	V
Average on-state current ( $T_c 049^\circ\text{C}$ )	$I_{T(AV)}$	7.5	A
RMS on-state current ( $T_c 049^\circ\text{C}$ )	$I_{T(RMS)}$	12	A
Non repetitive surge peak on-state current ( $t_p=10\text{ms}, T_j=25^\circ\text{C}$ )	$I_{TSM}$	120	A
Non repetitive surge peak on-state current ( $t_p=8.3\text{ms}, T_j=25^\circ\text{C}$ )		132	
$I^2t$ value for fusing ( $t_p=10\text{ms}, T_j=25^\circ\text{C}$ )	$I^2t$	72	$\text{A}^2\text{s}$
Critical rate of rise of on-state current ( $I_G=2 \times I_{GT}, f=100\text{Hz}, T_j=125^\circ\text{C}$ )	$di/dt$	100	$\text{A/s}$
Peak gate current ( $t_p=20\text{ }\mu\text{s}, T_j=125^\circ\text{C}$ )	$I_{GM}$	4	A



JCT151H-800R

JieJie M

FIG.1: Maximum power dissipation versus RMS on-state current



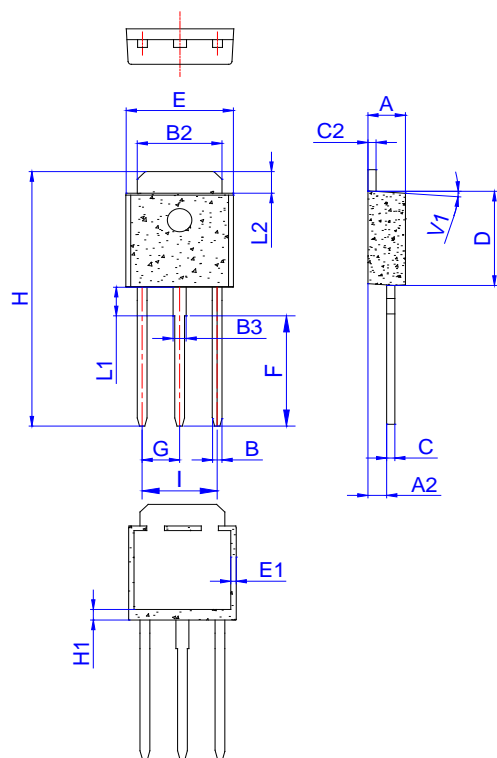
FIG.2: RMS on-state current versus case temperature

FIG.7 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards.





PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	1.00		1.30	0.039		0.051
B	0.50		0.70	0.020		0.028
B2	5.10		5.40	0.200		0.213
B3	0.70		1.00	0.028		0.039
C	0.45		0.62			
C2	0.48					
D						
E	6.40		6.70	0.252		0.264
E1	0.60		1.00	0.024		0.039
F	6.90		7.30	0.272		0.287
G	2.20			0.087		
H	16.00		17.00	0.630		0.669
H1	1.45		1.85	0.057		0.073
I	4.40		4.80	0.173		0.189
L1						
L2	1.25		1.55			
V1						

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